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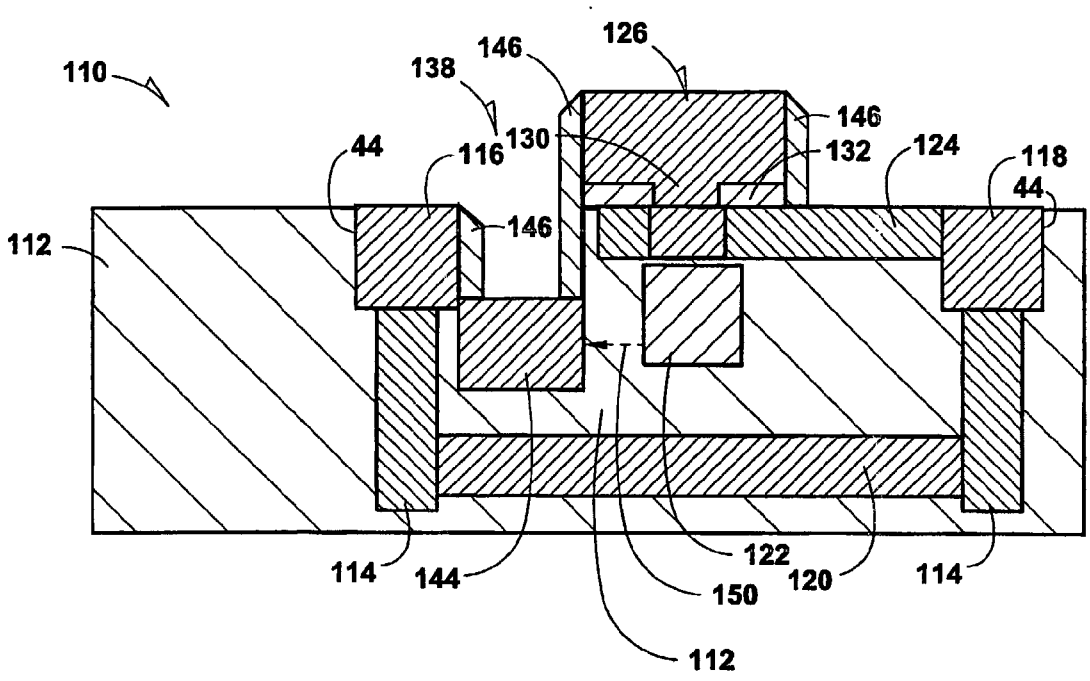
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(54) Title: SUPER SELF-ALIGNED COLLECTOR DEVICE FOR MONO-AND HETERO BIPOLAR JUNCTION TRANSISTORS, AND METHOD OF MAKING SAME



(57) Abstract: The invention relates to a process of forming a compact bipolar junction transistor (BJT) that includes forming a self-aligned collector tap adjacent the emitter stack and an isolated structure. A base layer is formed from epitaxial silicon that is disposed in the substrate.

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